

Silicon Bridge Rectifier

$$V_{RRM} = 50 \text{ V} - 1000 \text{ V}$$

$$I_F = 4 \text{ A}$$

Features

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Types up to 1000 V V_{RRM}
- Ideal for printed circuit board
- High surge overload rating
- High temperature soldering guaranteed: 250°C/ 10 seconds, 0.375(9.5mm) lead length
- Glass passivated chip junction
- High case dielectric strength 1500 V_{RMS}

GBU Package



Mechanical Data

Case: Molded plastic body over passivated junctions

Mounting position: Any

Terminals: Plated leads, solderable per MIL-STD-750

Method 2026 guaranteed

Maximum ratings, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	GBU4J	GBU4K	GBU4M	Unit
Repetitive peak reverse voltage	V_{RRM}		600	800	1000	V
RMS reverse voltage	V_{RMS}		420	560	700	V
DC blocking voltage	V_{DC}		600	800	1000	V
Continuous forward current	I_F	$T_C \leq 100^\circ\text{C}$	4	4	4	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25^\circ\text{C}$, $t_p = 8.3 \text{ ms}$	150	150	150	A
Operating temperature	T_j		-55 to 150	-55 to 150	-55 to 150	°C
Storage temperature	T_{stg}		-55 to 150	-55 to 150	-55 to 150	°C

Electrical characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	GBU4J	GBU4K	GBU4M	Unit
Diode forward voltage	V_F	$I_F = 4 \text{ A}$, $T_j = 25^\circ\text{C}$	1.1	1.1	1.1	V
Reverse current	I_R	$V_R = 50 \text{ V}$, $T_j = 25^\circ\text{C}$ $V_R = 50 \text{ V}$, $T_j = 125^\circ\text{C}$	5 500	5 500	5 500	μA

Thermal characteristics

Thermal resistance, junction - case	R_{thJA}		22.0	22.0	22.0	°C/W
	R_{thJL}		4.2	4.2	4.2	

